IPG16N10S4L61AATMA1-CN

100V/25A Dual N-Channel Advanced Power MOSFET

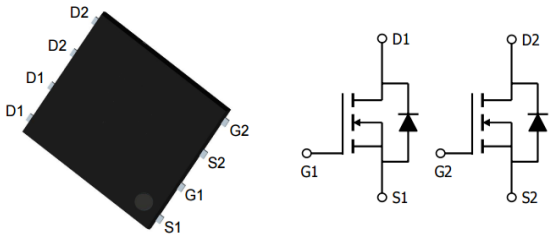
Features

- Dual N-Channel，*Low $R_{DS(on)}$ @V_{GS}=10V*
- *5V Logic Level Control*
- *100% UIS Tested*
- *Green Device Available*

$V_{(BR)DSS}$	$R_{DS(ON)}$ Typ	I_D Max
100V	33mΩ @ 10V	25A
	39mΩ @ 6V	

Applications

- Quick Charger
- *Load Switch*
- LED backlighting
- Telecom
- *I*ndustrial power supplies



PDFN5X6-Dual

Order Information

Product	Package	Marking	Packing
IPG16N10S4L61AATMA1-CN	PDFN5X6-Dual	040M10	4000PCS/Reel

Absolute Maximum Ratings

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Symbol	Parameter		Rating	Unit
Common Ratings (T_j=25°C Unless Otherwise Noted)				
V_{GS}	Gate-Source Voltage		±20	V
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage		100	V
T_J, T_{STG}	Junction and Storage Temperature Range		-50 to 175	°C
Mounted on Large Heat Sink				
I_{DM}	Pulse Drain Current Tested①	T_C=25°C	54	A
I_S	Diode continuous forward current	T_C=25°C	25	A
I_D	Continuous Drain Current	T_C=25°C	25	A
		T_C=70°C	20	
P_D	Maximum Power Dissipation	T_C=25°C	44.6	W
EAS	Avalanche energy, single pulsed ②		28.8	mJ
$R_{\theta JC}$	Thermal Resistance-Junction to Case		2.8	°C/W

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V I_D=250μA	100	110	--	V
I_{DSS}	Zero Gate Voltage Drain Current(T_C=25℃)	V_{DS}=100V, V_{GS}=0V	--	--	1	μA
	Zero Gate Voltage Drain Current(T_C=125℃)	V_{DS}=80V, V_{GS}=0V	--	--	100	uA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=+20V, V_{DS}=0V	--	--	±100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	1.0	1.6	2.5	V
$R_{DS(ON)}$	Drain-Source On-State Resistance③	V_{GS}=10V, I_D=8A	--	33	40	mΩ
$R_{DS(ON)}$	Drain-Source On-State Resistance③	V_{GS}=6V, I_D=5A	--	39	50	mΩ
$R_{DS(ON)}$	Drain-Source On-State Resistance③	V_{GS}=4.5V, I_D=4A	--	47	65	mΩ
Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
C_{iss}	Input Capacitance	V_{DS}=50V, V_{GS}=0V, f=1MHz	--	530	--	pF
C_{oss}	Output Capacitance		--	116	--	pF
C_{rss}	Reverse Transfer Capacitance		--	4.4	--	pF
R_g	Gate Resistance	f=1MHz		22		Ω
Q_g	Total Gate Charge	V_{DS}=50V I_D=10A, V_{GS}=10V	--	11.3	--	nC
Q_{gs}	Gate Source Charge		--	1.7	--	nC
Q_{gd}	Gate Drain Charge		--	3.7	--	nC
Switching Characteristics @ T_J = 25°C (unless otherwise stated)						
$t_{d(on)}$	Turn on Delay Time	V_{DD}=50V, I_D=5A, R_G=6Ω, V_{GS}=10V	--	7.6	--	ns
t_r	Turn on Rise Time		--	3.8	--	ns
$t_{d(off)}$	Turn Off Delay Time		-	23.2	--	ns
t_f	Turn Off Fall Time		--	5.4	--	ns
Source Drain Diode Characteristics @ T_J = 25°C (unless otherwise stated)						
V_{SD}	Forward on voltage③	I_{SD}=4A,V_{GS}=0V	--	0.81	1.2	V

Notes: ① Pulse width limited by maximum allowable junction temperature

② Limited by TJmax, starting TJ = 25°C, L = 0.1mH,RG = 25Ω, IAS = 24A, VGS =10V. Part not recommended for use above this value

③ Pulse width ≤ 300μs; duty cycle≤ 2%.

Typical Characteristics

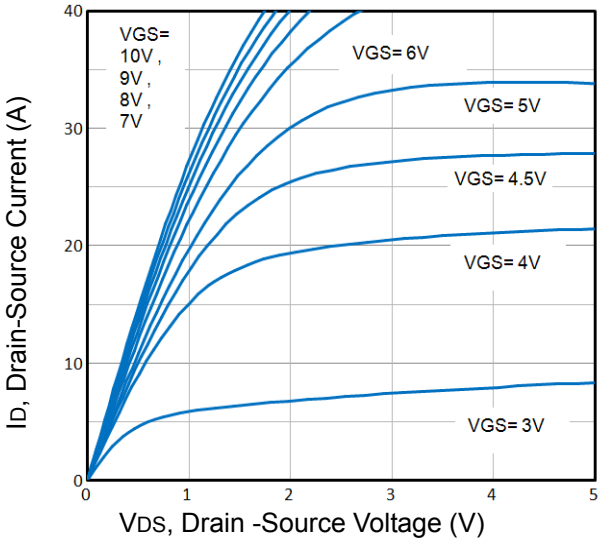


Fig1. Typical Output Characteristics

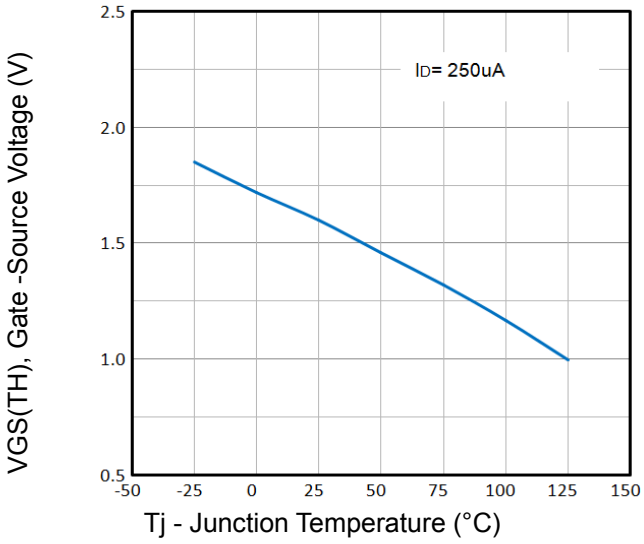


Fig2. VGS(TH) Voltage Vs. Temperature

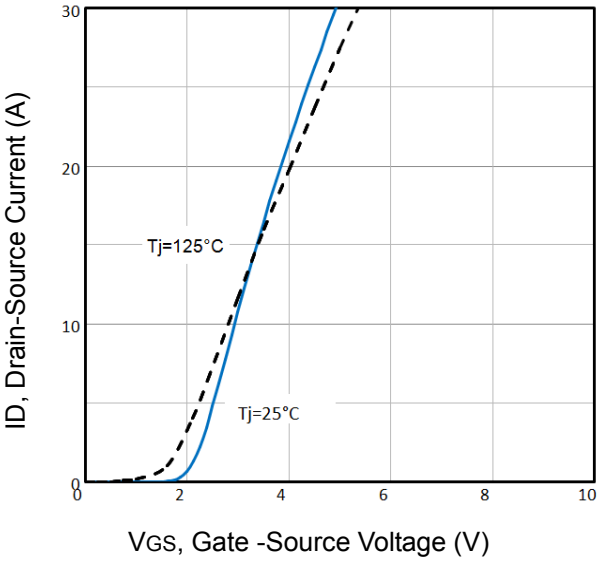


Fig3. Typical Transfer Characteristics

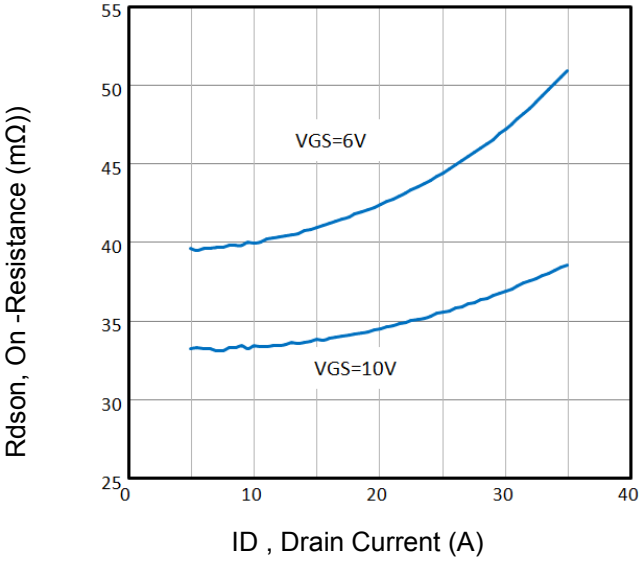


Fig4. On-Resistance vs. Drain Current and Gate Voltage

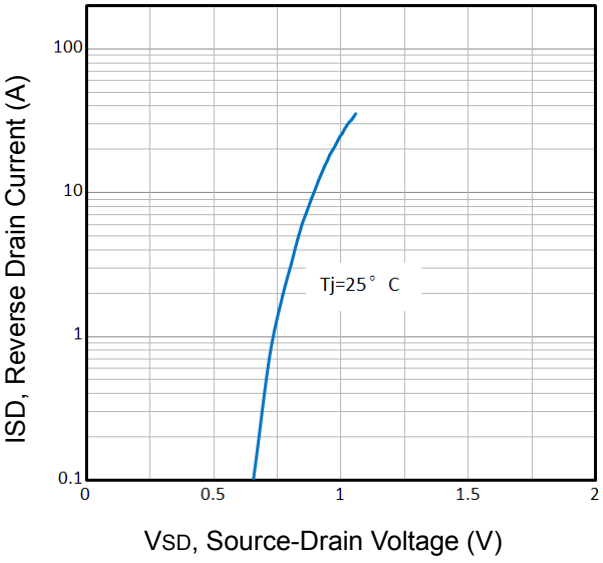


Fig5. Typical Source-Drain Diode Forward Voltage

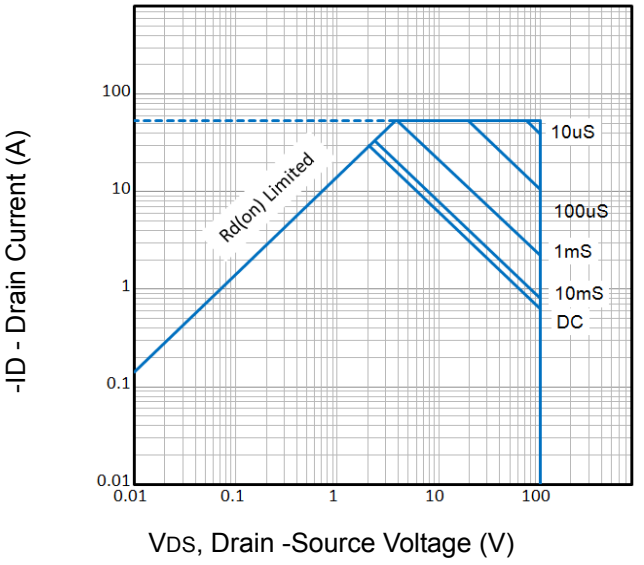


Fig6. Maximum Safe Operating Area

Typical Characteristics

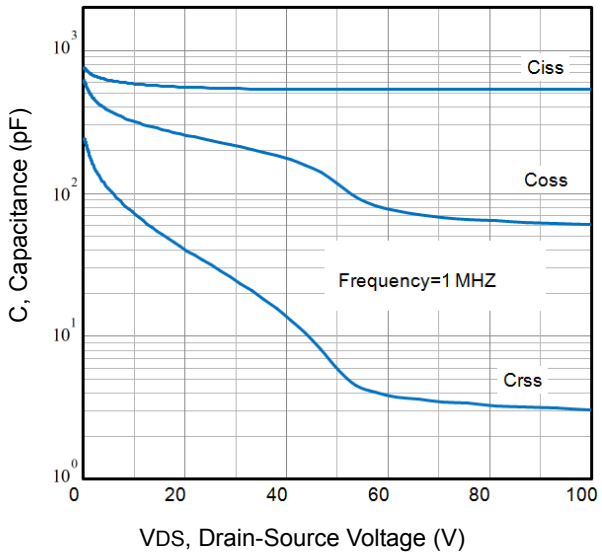


Fig7. Typical Capacitance Vs. Drain-Source Voltage

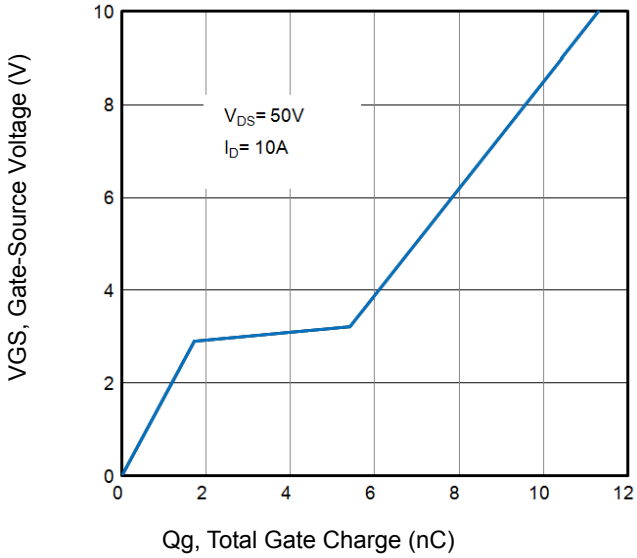


Fig8. Typical Gate Charge Vs. Gate-Source Voltage

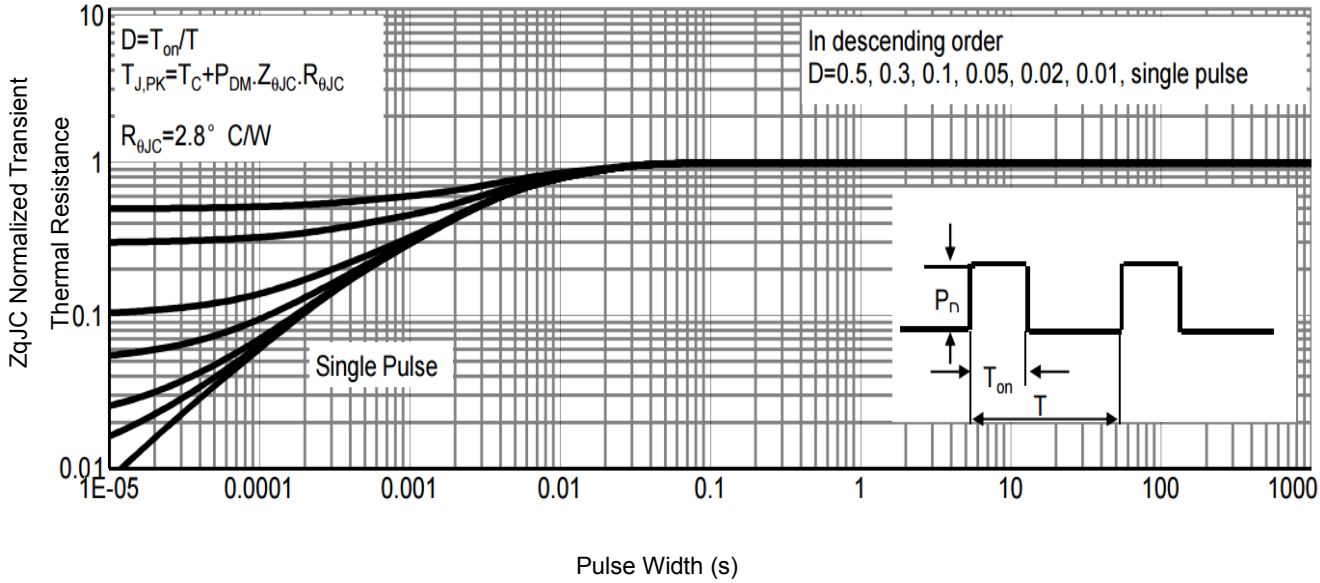


Fig9. Normalized Maximum Transient Thermal Impedance

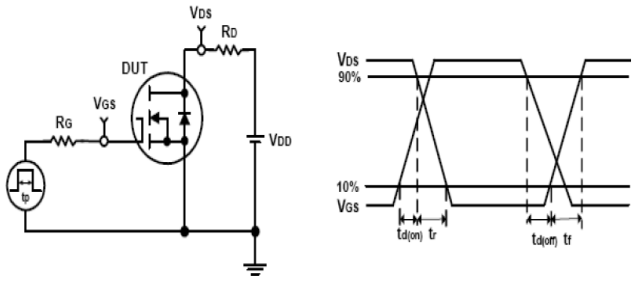


Fig10. Switching Time Test Circuit and waveforms

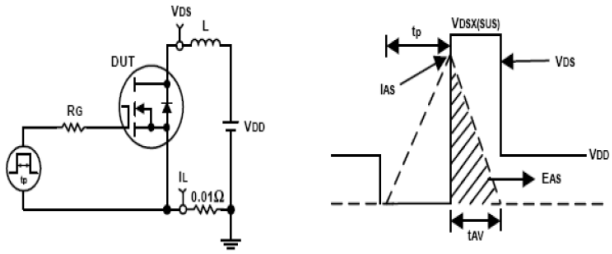
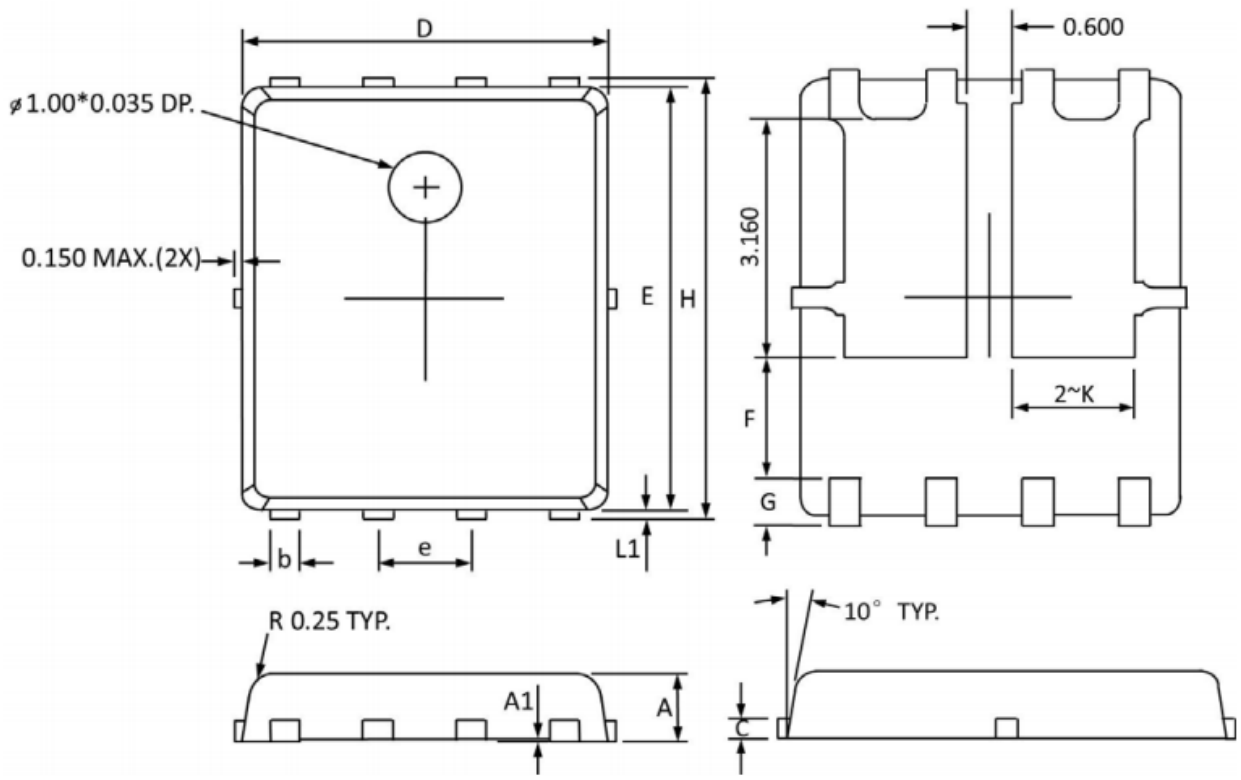


Fig11. Unclamped Inductive Test Circuit and waveforms

DFN5X6 Dual Mechanical Data



DIMENSIONS (unit : mm)

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	0.80	0.90	1.05	**A1**	0.000	--	0.005
b	0.35	0.42	0.49	**C**	--	0.254 Ref	--
D	4.90	5.00	5.10	**E**	5.70	5.80	5.90
e	--	1.27 BSC	--	**F**	--	1.60 Ref	--
G	--	0.60 Ref	--	**H**	5.95	6.12	6.20
L1	0.10	0.14	0.18	**K**	--	1.60 Ref	--

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